

AMENDMENTS TO THE SPECIFICATION:

Please amend the title as follows:

--SEMICONDUCTOR DEVICE AND METHOD OF FABRICATION SAME
WITH BONDING PAD SUPPORT STRUCTURE--

Page 9, replace the paragraph beginning on line 6 with the following amended paragraph:

--Referring now to FIG. 2A, the semiconductor device of the present working example includes upper copper layer 100 for improving shock resistance, this upper copper layer 100 being formed below bonding pad 130 that includes a metal film having aluminum (Al) as its chief component, a barrier metal being interposed between upper copper layer 100 and bonding pad 130. The barrier metal is provided for preventing the aluminum that is contained in bonding pad 130 from reacting with elements that are contained in the upper layer. ~~Lower~~ Upper copper layer 100 and bonding pad 130 have substantially identical planar dimensions (meaning that the planar dimensions are identical within the range of fabrication error); and upper copper layer 100 uniformly supports bonding pad 130 from below.--

Page 10, replace the paragraph beginning on line 21 and bridging pages 10 and 11 with the following amended paragraph:

--Laminated dielectric film 14, which is composed of a ladder-oxide film and a silicon dioxide (SiO₂) film, is interposed between the copper layer patterns of first lower copper layer 210. The ladder-oxide film in this case is ~~L-O*~~

L-OX, (a trademark of NEC Electronics Corporation (now in the application process)), which is a low-k film having a ladder-type hydrogenated siloxane. Laminated dielectric film 24 that is composed of ~~L-OX~~ L-OX film and a silicon dioxide (SiO_2) film is similarly interposed between the copper layer patterns in second lower copper layer 220. Forming laminated dielectric films 14 and 24 from dielectric films ~~(L-OX films)~~ (e.g., L-OX films) composed of a second material that has a lower relative dielectric constant than the first material reduces the capacitance between interconnects of the copper interconnects that are formed on the same level as lower copper layer 200.--

Page 17, replace the paragraph beginning on line 23 and bridging pages 17 and 18 with the following amended paragraph:

--In addition, the provision of a copper layer below bonding pad 130 allows the ultrasonic waves for realizing eutectic bonding of a gold wire and bonding pad 130 during bonding to be adequately transmitted to the gold wire and bonding pad 130 without being absorbed by a low-k film such as an ~~L-OX~~ L-OX film. As a result, the close adhesion of gold wires and bonding pads is strengthened and the wire-pull strength is increased.--

Page 18, replace the paragraph beginning on line 3 with the following amended paragraph:

--In addition, the actual metal film thickness of the bonding pad portion is the total thickness of the aluminum and

the copper layer below the bonding pad, whereby the hardness against probing and bonding is further increased. As a result, the load applied in the vicinity of the underlying ~~L-O*~~ L-OX film can be reduced and the occurrence of cracks in the interlevel dielectric film can be prevented.--